P hases interm ediate between the two dimensional electron liquid and W igner crystal

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We show that there can be no direct rst order transition between a Ferm i liquid and an insulating electronic (W igner) crystalline phase in a clean two-dimensional electron gas in a metaloxide-sem iconductor eld-e ect transistor (M O SFET); rather, there must always exist intermediate \m icro-emulsion" phases, and an accompanying sequence of continuous phase transitions. A mong the intermediate phases which we nd are a variety of electronic liquid crystalline phases, including stripe-related analogues of classical smectics and nematics. The existence of these phases can be established in the neighborhood of the phase boundaries on the basis of an asymptotically exact analysis, and reasonable estimates can be made concerning the ranges of electron densities and device geometries in which they exist. They likely occur in clean SiM O SFETs in the range of densities in which an \apparent m etal to insulator transition" has been observed in existing experiments. We also point out that, in analogy with the Pom aranchuk e ect in ³He, the W igner crystalline phase has higher spin entropy than the liquid phase, leading to an increasing tendency to crystallization with increasing temperature!

In discussions of the theory of the two dimensional electron gas (2DEG), it is generally accepted that, as a function of electron density n, there is a rst order quantum (T = 0) phase transition from a high density liquid [1] to a low density W igner crystalline phase[2]. This assum ption is reasonable in the case of a triangular W igner crystaldue to the presence of cubic invariants in the Landau free energy $[\beta]$, and for other lattices due to the general expectation [6] that uctuations will always render a freezing transition st order. The transition is thought $[n(a_B)^2]^{1=2}$ to occurwhen the dimensionless ratio r_s exceeds a critical value [7] $r_s = r_c$ 38, where a is the e ective Bohr radius in the sem iconductor. How ever, this generally accepted picture is manifestly incorrect for the 2DEG in a metal-oxide-sem iconductor eld e ect transistor (MOSFET), and possibly more generally!

Each electron in the 2DEG in a clean MOSFET drags along with it an image charge in the ground-plane above. Consequently, at small separations, the interaction between the electrons is the V (r) ể= r C oulom b inter− action, while for separations larger than the distance to the gate, d, it is the repulsive dipole-dipole interaction, $4e^{2}d^{2} = r^{3}$. (Here is the dielectric constant of V (r) the host sem iconductor.) In 2D systems with dipolar interactions, the following simple argument leads to the concussion that st order phase transitions are forbidden: In system s with interactions that fall m ore rapidly than $1=r^2$, there exists a \forbidden" range of densities in the neighborhood of a rst order phase transition where m acroscopic phase separation reduces the free energy of the system. However, when we come to compute the surface tension between two macroscopic phases, we nd that 1=r³ interactions are m arginal: for shorter range interactions, there is a well de ned scale independent surface tension, , while for longer range interactions, is scale dependent. Speci cally, for dipolar interactions, the interfacial contribution to the free-energy of an arbitrary m acroscopic m ixture of two phases is (see, e.g. [4, 5])

$$F = ds_{0}(\hat{}) - \frac{1}{2}^{2} \frac{dl}{p} \frac{dl}{l} \frac{dl}{l}$$
(1)

Here, the arclength integral, ds, runs along [8] the interfaces between the two phases, $\hat{}$ (s) is the local orientation of the interface, $_0$ ($\hat{}$) is the (in general orientation dependent and by assumption positive) short-range piece of the surface tension, dl runs along the interfaces [8], $_1 = 2e^2 (n)^2 d^2 =$, and n is the density di erence between the coexisting phases. The second (non-local) term in Eq. 1 comes from the long-range parts of the dipolar interaction. One can also view it as the leading nite size correction to the capacitance of parallel-plate capacitors due to the fringing elds [9].

It is important to note that the second term in Eq. 1 gives a negative contribution to the e ective surface tension which diverges logarithm ically with length; for example, an isolated straight segment of interface of length $L has F = L f_0$ $_1 \log [L=2d]g$. This implies that there is an absolute instability of the macroscopically phase separated state - in the regime of the phase diagram where a classical Maxwell construction would lead to two-phase coexistence, a state form ed from a microemulsion" of the two phases (with a character and length scale to be determined), has lower free-energy! Thus, instead of a rst order transition between two phases, there must always be an interm ediate regime in which one or more microemulsion phase occurs, bounded by one or more line of continuous phase transitions.

At this point we would like to compare this situation with the Coulomb case (no ground plane) where macroscopic phase separation is forbidden. The nature of the phases that result from the \C oulomb frustrated phase separation [10, 11]" in what would otherwise have been

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the forbidden range of densities is an issue of potentially relevance in m any highly correlated m aterials. However, the inhom ogeneities that occur in this situation are typically m icroscopic in scale, and so di cult to distinguish from m ore familiar charge density wave structures[19]. M oreover, the relevant m icroscopic details are di cult to treat with any degree of rigor. (It is an interesting[18] question, which we would like to reopen, whether there are interm ediate phases between the Ferm i liquid and W igner crystal phases in the 2DEG with pure Coulom b interactions.)

The character of the m icroem uslion of the two coexisting phases is determ ined by m inim izing F in Eq. 1; the result depends on how anisotropic the function $_0$ (^) is. The case where $_0$ (^) is independent of hasbeen considered in di erent contexts, including lipid Im s (e.g. Ref. [12]), two dimensional uniaxial ferrom agnets (e.g. [13]), and the 2DEG in MOSFET's [14, 15]. The resulting phase diagram includes both stripe and bubble phases, with stripes preferred in the center of the phase separated region and bubbles generally thought to be slightly low er in energy when one phase is in extrem e m inority. Current estimates[5] place the di erence between the dilute stripe and bubble energies at about 6%. In the earlier literature, it was assumed [12, 13] that there is a direct rst order transition between uniform stripe and bubble

phases. This is incorrect, even at mean-eld level, since, as we have shown, rst order phase transitions are forbidden. Thus, a sequence of continuous phase transitions (which we discuss below) must replace the putative rst order transition [14].

In the present case, where at least one of the two coexisting phases is crystalline, the angular dependence of $_0$ (^) is not negligible, rejecting the tendency of crystals to facet. C learly, a strong angle dependence of $_0$ (^) tends to facet stripe phases (where all interfaces lie along the direction in which $_0$ (^) is m inimal) relative to any form of bubble phase.

In the present paper, we characterize the phase diagram, and in particular the universal aspects of the interm ediate phases and phase transitions that are expected at low or zero temperature in an ideal MOSFET (i.e. in the absence any disorder). We will consider explicitly the case in which d is large compared to the spacing between electrons, nd² 1, as in this limit (as we shall see) uctuation e ects are param etrically sm all and an appropriatem ean- eld theory provides a valid zeroth-order description of the phases. In Sec. I, we rst discuss the mean-eld phase diagram, then in Secs. II and III we discuss the e ects of weak therm al and quantum uctuations, respectively. In Sec. IV, we discuss some of the in plications of the present results for the properties of real devices (which, alas, have non-negligible disorder), and in Sec. V we discuss some incompletely developed ideas concerning further in plications of the present line of analysis.

I. MEAN-FIELD PHASE DIAGRAM

Two dimensionless parameters determine the physics of the 2DEG in a MOSFET, r_s (de ned above) and $a_B = d$. Let us start with a discussion of the zero temperature mean-eld phase diagram of this system, assuming only uniform states. If nd^2 1, the free-energy per unit area can be represented by the sum $f(n) = f^{(C)} + f^{(el)}$ of the energy density of a capacitor $f^{(C)} = (en)^2 = 2C$ and the internal free-energy density of the electron liquid f (el). Here $C = (d)^{1}$ is the capacitance per unit area. At high electron densities, rs 1, the kinetic energy of the electrons is much larger than their potential energy, so the system forms a Fermi liquid. At small densities 1 (but still nd² 1) the Coulomb energy of the rs electrons is much larger than the kinetic energy, so the ground state is crystalline.

How ever, at even smaller densities when nd^2 1, the electrons interact only via dipole interactions, so the kinetic energy is larger than the potential, and the system again has a Ferm i liquid groundstate. (See discussion surrounding Eq. 12.) For $d=a_B$ 1, this im plies that the phase diagram of the system has reentrant transitions as a function of n (along the dasheddotted trajectory in Fig. 1) from a Fermi liquid phase for $n > n_c$ r_c^2 (a_B^2) ¹ to a W igner crystal phase for $n_c > n > n_{c1}$ (d) ¹, to a Ferm i liquid phase for $n_{\rm c1}$ > $\,n$. W ith decreasing d=a_B , $n_{\rm c1}$ and $n_{\rm c}$ m ove toward each other, until for $d < d_c = r_c a_B$, the W ignercrystal phase disappears entirely. This is represented by the dashed line in Fig. 1.

As a next step, we improve this phase diagram by allowing for the possibility of inhom ogeneous states. There is a range of forbidden densities about the critical density in which m acroscopic phase separation into regions of high and low density phase has lower free energy than the uniform state.

Let us brie y review the salient features of the M axwell construction for phase coexistence, as applied in the present context. For given average density, n, we consider a state in which a fraction, x, of the system is at a higher than average density, $n_+ > n$, and a fraction $(1 \ x)$ is at a lower than average density, n < n, such that $xn_+ + (1 \ x)n = n$. We then m inim ize the total free energy with respect to n_+ and n . The result of this m inim ization is an implicit expression for the densities of the two coexisting phases,

$$+ \frac{n_{+}}{C} = + \frac{n_{-}}{C} = \frac{[f(n_{-}) f(n_{+})]}{n};$$
 (2)

where = $0 f^{(el)}(n) = 0$ are the chem ical potentials in the two phases, and n [n₊ n]. Phase coexistence occurs for n < n < n₊, where the fraction of the two phases is determined by the lever rule,

+

$$x = (n \quad n) = n$$
: (3)

Eq. 2 is somewhat complicated, but it can be greatly simplied when the forbidden region is relatively small

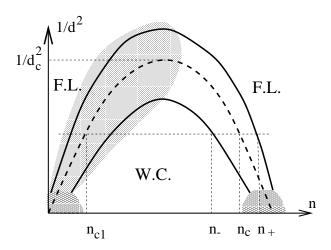


FIG.1: The T = 0 phase diagram of the 2DEG in an MOS-FET. The dashed line indicates the mean-eld critical density, n_c (d), where the free energies of the uniform W igner crystal (W C.) and Fermi liquid (F.L.) phases cross. The solid lines mark the boundaries of the regime of the intermediate microemulsion (stripe or bubble) phases. At mean-eld level, these solid lines are Lifshitz transitions. They approximately coincide with the regime of macroscopic two-phase coexistence $(n < n < n_{+})$ derived from a Maxwell construction. The hatched area represents the regime in which the regions of the two coexisting phases have sizes of order the electron spacing, so quantum uctuations are order 1, and hence may substantially alter the mean-eld character of the phases and phase transitions. The cross-hatched areas denote the regimes ofCoulomb frustrated phase separation where even the meaneld character of the phase diagram is not known.

 $(n n_c)$; in this case, we can linearize the density dependence of the free energy about the critical density,

$$f^{(el)}(n) = f^{(el)}(n_c)$$
 (n n_c) + ::: (4)

where ::: represents higher order terms in powers of $(n \quad n_c)$. To this level of approximation,

$$n = n_c \frac{n}{2}$$
; $n = \frac{(+)}{e^2 d}$: (5)

The discontinuity of the chem ical potential, (+) > 0, is determined by microscopic physics, and is only small to the extent that the putative transition is weakly rst order. Whether or not the transition is strongly rst order, for d large, n is self-consistently small.

The validity of the M axwell construction rests on the implicit assumption that the interface energy between the coexisting phases is positive, so the amount of interface is m inim ized. As we have seen, in the dipolar case this assumption is invalid. We can construct a state with lower free energy by making an inhom ogeneous mixture of the two coexisting phases to increase the amount of interface. To complete the mean eld analysis, one should minim ize Eq. 1 with respect to the shape of the minority phase regions at given area of the phase – the area being given, to rst approximation, by the M axwell rule.

A. Stripe Phases

To begin with, let us consider only striped phases. This is fully justimed in the case of strong anisotropy of the surface energy. (As we will see letter even in the opposite case when (^) is isotropic, there are regions in the phase diagram where this assumption is relevant.) The interfacial free energy density for a striped phase is easily computed from Eq. 1 to be

$$f = L^{1} f 2_{0} \quad 4_{1} \ln [L_{+} L = dL]g;$$
 (6)

where L are the widths of the high and low density regions, respectively, and $L = L_+ + L_-$ is the period of the stripe structure. M inimizing Eq. 6 at xed areal fraction of the high density phase, x $L_+ = L_+$, we get

$$L = \frac{d}{x}e^{1+}$$
; $L_{+} = \frac{d}{(1-x)}e^{1+}$ (7)

with = $_0=2_1$. It is important to note that as x ! 0, the stripes of the high density phase approach a nite limiting width, L_+ ! $L_0 = de^{1+}$, although the spacing between stripes, L, diverges in proportion to 1=x. A lso, because the minimized value of f = $4_1=L$ is negative, the region of stability of the striped phase in fact extends som ewhat beyond the edges (n and n_+) of the two-phase region derived from the M axwell construction.

Finally, it is necessary to estim ate the magnitude of ; if it is of order 1, then L_0 d, but if 1, then L_0 is exponentially larger than atom ic lengths. So long as the stripe phase occurs in a relatively narrow range of n, we can use Eq. 5 to estimate $_1$, with the result that j^2 , which is a ratio of m icroscopic $_{0}e^{2}=[+]$ electronic energies. Thus, except under special circum stances, we expect that 1, and hence that L_0 d. However, so long as nd^2 1, the stripe widths are still large compared to the spacing between electrons, which validates the macroscopic approach taken here.

In short, at m ean eld level, as a function of decreasing density the system evolves from the Ferm i liquid phase, through interm ediate stripe phases, to the W igner crystal, as sum m arized in Fig. 2a:

1) Starting in the uniform Ferm i liquid phase, as the density is varied across n_+ , the system undergoes a transition to a stripe phase, consisting of a periodic array of far separated stripes of W igner crystal, with characteristic width L_0 . This transition is analogous to a Lifshitz transition, in that the period of the ordered phase diverges at the transition [23]. Thus, the argum ents[6] that uctuations will generally drive an otherwise continuous freezing transition rst order do not apply; the continuous character of this transition is robust.

2) There is, of course, som e coupling between the translational motion of the crystalline order in neighboring stripes, so at mean-eld level the crystalline order will be locked from stripe to stripe.

C onsequently, the stripe ground-state breaks translation symmetry not only in the direction perpendicular to the stripes, but along the stripe direction as well. How ever, near the transition, where x 1, the spacing between stripes is large compared to L₀, so this coupling is exponentially sm all; consequently, this locking can be neglected for all practical purposes. Therefore, this phase should operationally be classi ed as an electron smectic [17], in which translation symmetry is unbroken along the stripe direction. (There remains the interesting academ ic question of principle whether or not quantum uctuations are able to truly stabilize this smectic phase at T = 0 - this is closely related to the issue of whether \ oating phases" are stable in quasi-1D electronic system s.[17, 22]).

3) Near x = 1=2, the stripes of W igner crystal and the intervening Ferm i liquid are comparable in width.Asx! 1, the system is better thought of as stripes of Ferm i liquid separated by broad regions of W igner crystal. At some point, the crystalline order becom es so rigid that the coupling across the liquid stripes is no longer negligible. At this point, the striped state is fully crystalline, in the sense that translation symmetry is broken in both directions, and the structure factor contains B ragg peaks. However, this phase is still qualitatively distinct from the W igner crystal. Since generally speaking the Ferm i wave vector is unrelated to the Bragg vectors of the W igner crystal, the liquid in the stripe \rivers" can still conduct current in the stripe direction. For want of a better name, we christen this state a striped \conducting crystall." (See Fig.2).

4) At x = 1, the transition from the conducting to W igner crystalm incors the smectic to Ferm i liquid transition; it is also a Lifshitz transition at which the period of the stripe order diverges.

B. Bubble Phases

So far, this analysis ignores the possibility of bubble phases. W hether or not there is a regime in which the lowest energy mean-eld state is a bubble phase depends, as we mentioned before, on the degree of anisotropy of the microscopic surface tension, $_0$ (^). It may happen, due to the anisotropy of the W igner crystal, that $_0$ (^) is su ciently anisotropic that bubble phases never intrude upon the phase diagram. It is also possible to force the issue by arti cially enhancing the anisotropy of $_0$ (^). This can be done by explicitly breaking the rotational symmetry of the 2DEG, for instance by applying an inplane magnetic eld or by using a su ciently anisotropic surface in the construction of the M O SFET. In this case, no m ore need be said.

stripe phase; for x near 0, such a phase consists of far separated crystallites in a metallic sea, while for x near 1, it is far separated bubbles of uid in a W igner crystalline host. W e will call these phases Bubble C rystals I and II, respectively. (See Fig.2d) As x ! 0 or x ! 1, the period of the bubble crystals diverge, leading at m ean-

eld level to another Lifshitz transition, much as in the stripe case. (However, uctuation e ects are much di erent near these transition in the bubble and stripe cases, as we will discuss in the next sections.)

However, this is not the end of the story. The stripe phase is always the lower energy one near x = 1=2, so if a bubble phase occurs for small x, there must be a critical value of $x = x_c$ at which the energy of the bubble and stripe phases cross, seem ingly in plying a rst order transition. Since we have proven in general that

rst order transitions are forbidden, this rst order transition, too, must be replaced by a regime of intermediate phases consisting of a mixture of bubble and stripe phases [14]. Now, however, because of the large anisotropy of the stripe phase, the surface tension between these two phases must be highly anisotropic. Thus, this intermediate phase will most probably be of the form of alternating mega-stripes of bubble and stripe phase regions. These regions are shown in Fig 2d by hatched boxes.

II. THERMALEFFECTS.

A. The Pom aranchuk E ect

The most dram atic e ect of nite T is its e ect on the balance between the liquid and W igner-crystalline phases – the fraction of the W igner crystal phase grows as the tem perature increases [14]! This phenom enon is sim ilar to the Pom eranchuk e ect in H e^3 and has the same origin: the spin entropy of the crystal phase is substantially larger than that of the liquid state. The same considerations lead, as well, to the conclusion that the crystalline phase is preferred relative to the liquid in the presence of an in-plane m agnetic edd, H_k.

Due to the Pauli exclusion principle, an elective exchange energy of order the Fermi energy, E_F fn=2m quenches the spin entropy in the liquid phase. In contrast, the exchange[25] energy in the W igner crystal is exponentially small, $J / \exp[\frac{P}{r_s}]$ where is a number of order 1. For example an estimate made in [20] yields J 10⁷Ry where Ry = e⁴m = 2 h²e is the effective Rydberg. Thus a combination of the quantum character of the liquid and the smallness of exchange processes in the solid in ply that the solid phase is stabilized by non-zero T relative to the liquid phase – for n near n_c, the 2D EG freezes upon heating! In the present context, this means that for xed n, the relative frac-

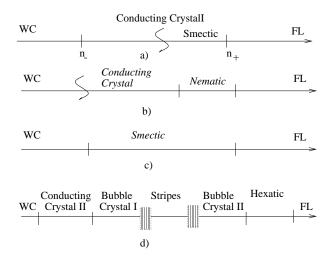


FIG. 2: Schematic representation of the sequence of intermediate states as the 2DEG evolves from the Fermi liquid (FL) to the W igner crystal (W C). In a, b, and c, we assume that () is su ciently an isotropic that bubble phases are supressed. a) Them ean-eld phase diagram . Under appropriate circum stances, this also represents the true sequence of phase transitions at T = 0.b) The phase diagram at non-zero tem perature with a rotationally invariant Hamiltonian. c) The phase diagram at non-zero tem perature with a preferred axis, for instance due to an in-eld magnetic eld. Vertical lines represent phase transitions and wavy lines crossovers. Phases with power-law order are named in italics. The smectic phase in a) is weakly unstable to crystallization at mean-eld level, but m ay be stabilized by quantum uctuations. d) The phase diagram including bubble phases at T = 0 in the presence of quantum uctuations. The hatched areas correspond to the sequence of transitions involving mega-stripes of bubble and stripe phases discussed in the text.

tion of W igner crystalline regions increases with increasing T or H_k. A simple estimate of the magnitude of this e ect can be made for the range of temperatures J T $E_F = Ry = (r_s)^2$ and $h_B H_k = E_F$, where the entropy of the liquid is negligible, as are the subtleties of the ground-state magnetic structure of the W igner crystal. In this case,

$$f(n;T;H_k)$$
 $f(n;0;0)$ (8)
 $k_B T n \ln 2 \cosh(h_B H_k = k_B T)$

and f $(n_+;T;H_k)$ f $(n_+;0;0)$. The fact that tem perature and m agnetic eld stabilize the W igner crystal in qualitatively sim ilar fashion is one of the striking aspects of this relation: For T $h_B H_k$, f $(n_;T;H_k)$ f $(n_;0;0)$ k Tn ln[2] while for T $h_B H_k$, f $(n_;T;B)$ f $(n_;0;0)$ $h_B H_k n$.

O f course, at high enough tem peratures, all tendencies to ordered states are suppressed. This occurs above the characteristic tem perature at which the W igner crystal m elts. In the limit of very large r_s , this occurs at the classical m elting tem perature of the W igner crystal, which has been estimated in accurate num erical

experiments[21] to be

$$T_{m elt} = A (e^2 =)^{p} \overline{n} = 2ARy = r_s$$
(9)

where A = 1=125 [l 0:04]. However, at smaller g, where E $_{\rm F}$ of the competing uid phase is larger than the putative classical melting temperature, the implied reduction of the entropy of the uid state means that the melting temperature is set, by $T_{\rm m\ elt}$ / $E_{\rm F}$. Far from the Lifshitz points, the melting temperatures of the various microemulsion phases are determined by these same considerations, and are of similar magnitude. Here, the fraction of the system that is crystalline is a non-monotonic function of T, rst increasing and then dropping to zero at $T_{\rm m\ elt}$. Near the Lifshitz points, more delicate considerations determine the melting point.

B. Therm al uctuations in the stripe phases

Let us now consider the role of thermal uctuations on the stripe phases. We distinguish two cases: 1) If the Ham iltonian is rotationally invariant, then the smectic phase is unstable at any non-zero temperature to the proliferation of dislocations. Thus,

the mean-eld smectic phase is replaced by a nem atic phase, which, in keeping with the Merm in-Wagner theorem, does not actually break rotational symmetry, but rather has power-law orientational order. A free dislocation has a logarithm ically divergent energy in both the W igner and conducting crystal phases, so they are robust against therm al uctuations at low tem peratures, although with power-law rather than long-range crystalline order. The resulting phase diagram is shown schem atically in Fig. 2b. 2) If, however, the Ham iltonian has a preferred axis, for instance if we consider the 2DEG in the presence of an in-plane magnetic eld, the e ects of low temperature thermal uctuations are much less severe. Here, the smectic and both crystalline phases remain well de ned at non-zero T, although again with power law spatial correlations rather than with true longrange order, as shown schem atically in Fig. 2c.

Because rst order transitions are forbidden, the transition between the isotropic uid and the nem atic phase must be of the Beresinskii-K osterlitz-Thouless (BKT) type. Near them ean eld Lifshitz point we can estimate this transition temperature as follows: The distance between stripes is large so the stripes of m inority phase evaporate when the energy to break o a piece, $_0L_0$, is less than the the con gurational entropy of a state where rare droplets of the m inority phase are distributed random ly. Equating these two free energies leads to the estimate

$$T_{c}jln[x(1 x)]j_{0}L_{0}$$
: (10)

In the presence of an in-plane magnetic eld, there is no sharply de ned nem atic phase, since rotational sym metry is explicitly broken. How ever, by the same token, free dislocations in the smectic state have a logarithm ically divergent energy, so a power-law smectic phase exists at non-zero T.W ith increasing temperature, the smectic to liquid phase transition is also of the BKT type. Indeed, so long as the symmetry breaking term in the Ham iltonian is small, the transition temperature is roughly the same as in Eq. 10, above.

C. Thermal uctuations in the bubble phases

We now consider the e ect of thermal uctuations on bubble phases. As can be seen from Eq. 1, the interaction energy between far separated bubbles decreases at large r_0 as

$$V_{\text{bubble}} \quad {}_{1}L_{0}^{4} = r_{0}^{3}; \qquad (11)$$

where L_0 and r_0 are the radius of and distance between bubbles. Thus, where the bubbles are far separated, because of the screening by the ground-plane the BKT melting temperature will tend to rapidly to zero, $T_{B\,K\,T} / [(1 \ x)x]^{=2}$, as the spacing between bubbles increases. The result is that, near the mean led Lifshitz point the bubble phase is always melted by the therm al

uctuations. On the other hand, at smaller 1, the bubble phase survives therm al uctuations in the usual sense that the correlations of bubble positions exhibit powerlaw decay.

The nature of the transition between the bubble phase and the uniform phase is not, presently, settled. Of course, a direct rst order transition is forbidden. One possibility is that there is a sequence of two BKT transitions, as in the Halperin-Nelson theory [29] of melting, with an intermediate hexatic phase. A Itematively, there may be a further set of hierarchical microem ulsion phases.

III. QUANTUM FLUCTUATIONS

A. Stripe Phases

1 (nd² So long as nL_0^2 1), the stripes are many electrons wide, so quantum uctuations of their positions are intrinsically small; $1=nL_0^2$ is a small parameter in the problem, which perm its an asymptotically exact treatment of quantum uctuation e ects. At zero tem perature, the conducting-crystal phase is clearly stable in the presence of sm all quantum uctuations, although, as m entioned previously, the jury is still out on whether the sm ectic phase is unstable to crystallization [17, 22]. Only where the stripe width is of order of the interelectron distance (i.e., when nL_0^2 1), quantum uctuations becom e very signi cant. This applies to the hatched region in Fig. 1, where the quantum properties of the system are still uncertain.

The quantum nature of the system near the Lifshitz points is determined by the quantum nature of the interface between the crystal and the liquid { a problem which itself is still unsolved. This interface may be quantum rough or quantum smooth. If it is smooth, the Lifshitz transition from the uniform uid to smectic phase is not fundamentally a ected by quantum uctuations, provided the width of the stripes is large enough. How ever, if an isolated interface is rough, the stripe order in the vicinity of the mean-eld Lifshitz point is quantum melted; in this case, for the rotationally invariant system, the proscription against st order transitions im plies that there must be an interm ediate zero tem perature nem atic phase between the isotropic and the stripe ordered phases. It was recently show n [18] that a nem atic Ferm i uid is necessarily a non-Ferm i liquid in the sense that quasiparticles are not well de ned elementary excitations. We believe that, depending on microscopic details and on the the value of nd², both scenarios are possible.

It is worth m entioning why the quantum nature of the crystal-liquid interface is so subtle. Consider the motion of a step in the interface. Quantum -m echanically, an isolated step might be expected to propagate along the interface [27]. Because the steps interact by a shortrange dipolar interaction, the steps should then form a delocalized 1D quantum liquid along the interface. How ever, because of the density m ism atch between the solid and liquid, the situation is more complicated. Motion of the step requires a ux of mass into the liquid of a magnitude proportional to the density di erence between the solid and liquid and to the step's velocity. In a Ferm i liquid this ux of m ass is carried by quasiparticles, m aking the step motion highly dissipative. Thus, characterizing the interface involves interesting, but as far as we know unsolved issues in dissipative quantum mechanics.

B. Bubble Phases

In contrast to stripe phases, quantum uctuations always melt the bubble phases when the bubbles are suf-

ciently dilute. To see this, we can estim ate the characteristic potential energy of a bubble crystal as in Eq. 11, and can make a corresponding dimensional estim ate of the bubble kinetic energy K _{bubble} $\hat{H}=r_0^2 m$ where m is the bubble e ective mass. Therefore the ratio of these energies is

$$\frac{V_{\text{bubble}}}{K_{\text{bubble}}} \qquad \frac{{}_{1}L_{0}^{4}m}{h^{2}} \quad \frac{1}{r_{0}}$$
(12)

vanishes as $r_0 ! 1$. This analysis eshes out the same argumentmentioned in the introduction that leads to the conclusion that there is no stable W igner crystalphase at smalld. However, whereas in that case, the proportionality constant is a_B , in the present case the same constant is parametrically large, both due to the explicit factors of L_0 and due to the fact that m increases with increasing

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 $\rm L_0$ (in a way that depends on whether the interface is quantum rough or smooth). The result is that, for large nd², the regime in which the bubble crystal is quantum melted is extremely small. However, if nd² 1 quantum melting is a signi cant phenom enon.

The character of the bubble liquid phase is di erent depending on the character of the m inority phase. When the majority phase is W igner-crystalline with dilute inclusions of liquid, the melting of the bubble crystal results in a type of \conducting crystal" [14]. In this state, crystalline long-range order coexists with uid-like conductivity, but in this case the conductivity is associated with the motion of the bubbles them selves. Phenom enologically this state is similar to the \supersolid" phase which has been discussed [28] in the context of H e⁴. In both cases the number of electrons (or arom s) is not equal to the number of the crystalline sites. [31]. The di erence is that unlike the case of H e⁴ where vacancies are bosons, in our case the statistics of the droplets is not known, and hence the liquid state may not be a super-

uid. Therefore, we refer to this state as a "C onducting C rystal II" in Fig2d to distinguish it from the highly anisotropic conducting crystal (See Fig2a,d) which originates from the existence of stripes.

W hen the Ferm i liquid is the majority phase, with a uid of \icebergs" oating in it, no spatial symmetries need be broken. However, elementary excitation spectrum is likely to be dierent from that of a conventional Ferm i liquid.

Since the majority phase already brakes rotational symmetry, the bubble crystallization transition which transforms the system from the conducting crystal to the insulating bubble crystal phase can be a simple continuous transition. However, the freezing of the icebergs into a triangular crystal of W igner-crystalline bubbles is more problem atic. As with the therm al transition, there may be a two-step freezing transition, with an interm ediate quantum hexatic phase[18], or another hierarchy of microem ulsion phases. The sequence of the phases at T = 0 is shown in Fig.2d.

IV. EXPERIMENTAL CONSEQUENCES

O bviously, there are m any experim ental consequences of the existence of interm ediate phases, of which we here list only a few. It should be kept in m ind that m acroscopic spatial symmetry breaking, the sort which precisely characterizes the various phases we have discussed, does not truly occur in 2D in the presence of quenched disorder. This com plicates the actual observation of various phenomena.

The majority of industrially produced SiMOSFET's have gates relatively close to the 2DEG, d d_c , so the electron liquid is weakly interacting at all n. However, a small number of high mobility SiMOSFET's (For a review, see [30].) and p-type of GaAs double layers [32] with large d 1000A have been studied in the past few

years, and found to exhibit transport anom alies that have been interpreted as evidence for an unexpected m etalinsulator transition. W hile these devices certainly are not ideal, in the sense that they have non-zero quenched disorder, we would like to propose that a natural explanation of these phenom ena is that they re ect the existence in the zero disorder limit of the electronic m icroem ulsion phases identied in the present paper.

One robust consequence of two-phase coexistence is that the conductivity is a decreasing function of the volum e fraction of W igner crystal. This volum e fraction, in turn, is strongly temperature and magnetic eld dependent due to the Pomeranchuk e ect, as explained above. As a result, the fraction of crystal grows with tem perature and m agnetic eld, leading to a corresponding increase of the resistivity. As has been pointed out previously [14], this basic physics m ay underly the transport anom alies observed in large d SiM O SFETs. In particular, it o ers a candidate explanation of the anom alous m etallic (d =dT > 0) tem perature dependence and large positive m agneto-resistance observed in these system s despite the fact that the resistivity, itself, exceeds the Io e-Regellimit. (Ideally, one might want to explore the scaling relation between the tem perature and magnetic eld dependence of the resistivity in plied by the therm odynam ic relation in Eq. 9.)

Of course, each new phase has di erent patterns of spatial sym m etry breaking, and hence has new collective modes and modi ed hydrodynamics. Even when the effects of quenched disorder or thermal uctuations restore the symmetry at macroscopic distances, the existence of these collective modes can have readily detectable consequences for the dynam ical responses of the system . Sm all explicit symmetry breaking elds can be used to overcome the destructive e ects of quenched disorder and reveal the true tendency to symmetry breaking. For instance, an in-plane magnetic eld explicitly breaks rotational symmetry; where some form of stripe or nem atic phase exists in the absence of quenched disorder, the small symmetry breaking produced by such a eld can give rise to a large resistivity an isotropy, as has been seen for the analogous states in quantum Halldevices [24].

V. EXTENSIONS

W e end with som e speculative observations concerning interm ediate phases of the 2D $\rm E\,G$.

Spin physics: 0 ther than the Pom eranchuk e ect, we have largely ignored the physics of the electron spins. The exchange interactions in the W igner crystal phase are generally found to be very sm all[25], and so are only important at very low temperatures. At T = 0, how-ever, the fact that the magnetic H am iltonian is highly frustrated and may have important multispin ring exchange interactions, can lead to a variety of possiblem agnetic phases, and this com plexity could be inherited, to some degree, by the interm ediate phases discussed here.

M oreover, at a liquid-crystalline interface, the quantum dynam ics of the interface itself (m entioned above) can produce e ective exchange interactions, likely with m uch larger energy scales than in the bulk W igner crystal. There is thus the very real possibility that the m agnetic structure of the interfaces is very rich, and characterized by substantial energy scales.

Superconductivity: The parallels between the 2DEG in a M O SFET and C oulom b frustrated phase separation in a doped M ott insulator naturally lead one to speculate concerning the possibility of superconductivity in the present system. In the bubble related conducting crystal phase, each bubble has a xed number of electrons; when that number is even, the bubbles are likely bosonic and a supersolid phase with low super uid density is possible [14, 28]. In the hatched region of the phase diagram, where quantum e ects are most severe, a more robust mechanism is possible, based on the \spin-gap proximity e ect [26]": Sm all clusters of W igner crystal (be they stripe or bubble like) will offen have a spin-gap. (Near the cluster edge, this gap may be larger than in the bulk.) W here this gap is large enough, it suppresses single-particle exchange between the crystal clusters and the surrounding Ferm i uid, but pair-exchange is still perm itted. W hen this dom inates, it induces global superconductivity by a process analogous to the conventional proximity e ect.

Double Layers: In a double layer system, with two nearby 2D EG's, the two layers screen each other in much the same way as the metal layer screens the 2D EG in a M O SFET. However, here the types of phases, and the available experiments are still richer. One particularly interesting point is that the conductivity measured in drag can explore the nature of the interlayer screening. The presence of a crystalline component of an electron uid has the potential to greatly increase the drag conductivity relative to a Ferm i liquid; in particular, whereas the drag conductivity vanishes as T ! 0 in a Ferm i liquid, we believe it can approach a non-zero constant in som e of the interm ediate phases we have explored.

O ther Applications: The present ideas are pretty clearly applicable in a host of additional physical contexts. W hat is needed is short-range tendency to phase separation, i.e. a concave local free energy, opposed by dipolar forces. Under appropriate circum stances, this situation may pertain in the 2DEG at higher densities, $r_s < r_c$, and it certainly applies in various regimes to the physics of lipid lines and planar ferrom agnets.

A cknow ledgem ents: This work was supported in part by the NationalScience Foundation under Contracts No.DMR-01-10329 (SAK) and DMR-0228104 (BS).

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